NSN 5961-01-580-9270

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-580-9270 **Inclosure Material:** Plastic **Overall Length:** Between 2.8 millimeters and 3.0 millimeters **Overall Height:** 1.1 millimeters **Overall Width:** Between 1.5 millimeters and 1.7 millimeters **End Application:** Ca70608-0019191560, receiver-transmitter Joint Electronic Device Engineering Council/jedec/case Outline Designation: Mo-193, var. Aa, issue c, dated january 2000 **Component Name And Quantity:** 2 transistor **Mounting Method:** Press fit **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 30.0 collector to emitter voltage, dc all transistor and 60.0 collector to base voltage, dc all transistor and 5.0 emitter to base voltage, dc all transistor **Current Rating Per Characteristic:** 500.00 milliamperes collector current, dc all transistor **Power Rating Per Characteristic:** 700.0 milliwatts total power dissipation all transistor **Product Name:** Dwg - cage 19156: transistor array, general purpose amplifier; datasheet - cage 7d893: npn and pnp general purpose amplifier **Special Features:** Case: super sot-6; transistor type: c1, b1, e1: npn; c2, b2, e2: pnp; operating and storage junction temp range: -55.0 to +150.0 degrees c **Terminal Type And Quantity:** 6 tab, solder lug Shelf Life: N/a **Unit Of Measure:**

Demilitarization:

Yes - demil/mli

Fiig:

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